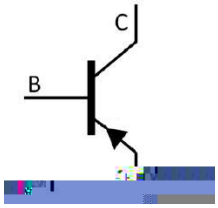
Rev.E Sep.-2016

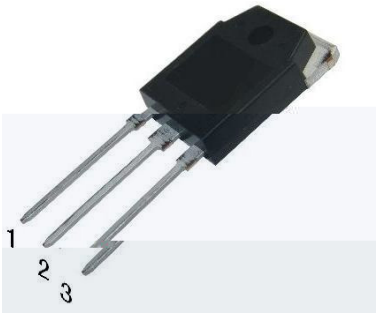
TO-3P PNP Silicon PNP transistor in a TO-3P Plastic Package.

200W MJW21194

Recommend for 200W high fidelity audio frequency amplifier output stage, Complementary to MJW21194.

Power amplifier applications.



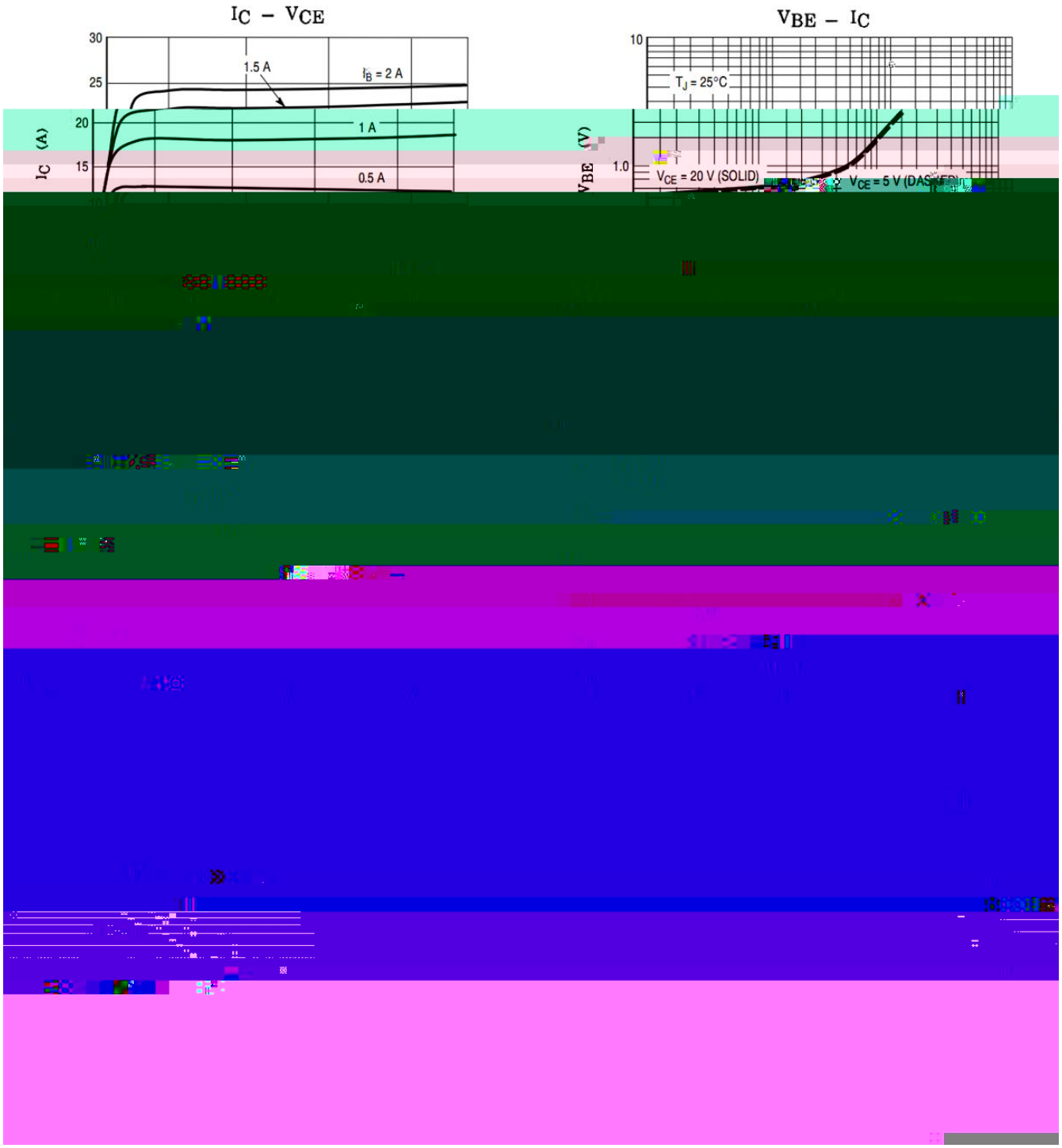


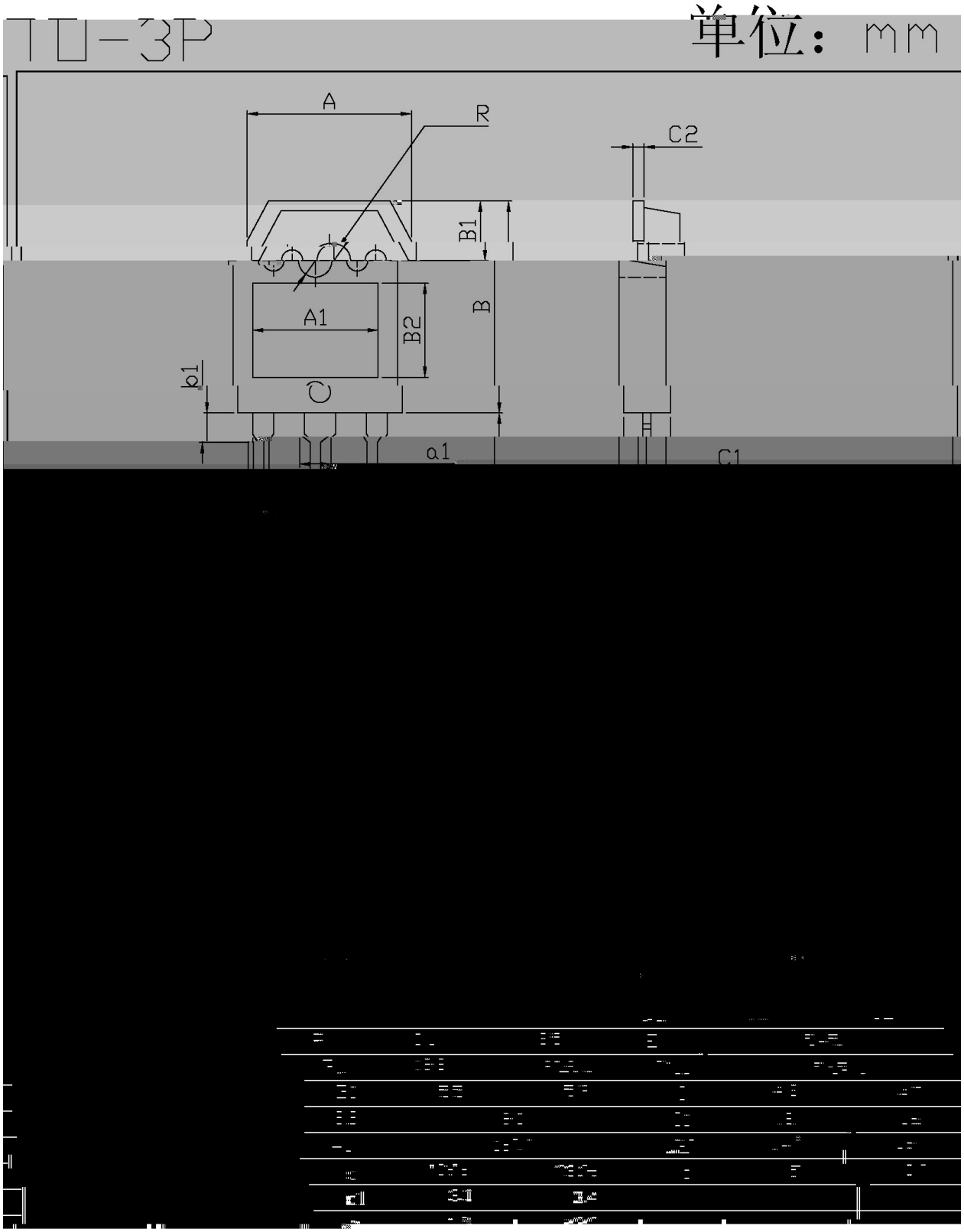
PIN1 Base PIN 2 Collector PIN 3 Emitter

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-400	V
Collector to Emitter Voltage	V_{CEO}	-250	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-16	A
Peak Collector Current	I_{CP}	-30	A
Base Current	I_B	-5.0	A
Collector Power Dissipation	P_C(TC=25)	200	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CEO}	I_C=-100mA I_B=0	-250			V
Collector Cut-Off Current	I_{CEO}	V_{CE}=-200V I_E=0			-100	A
Collector Cut-Off Current	I_{CBO}	V_{CB}=-250V I_E=0			-100	A
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-100	A
DC Current Gain	$h_{FE(1)}$	V_{CE}=-5.0V I_C=-8.0A	10		80	
	$h_{FE(2)}$	V_{CE}=-5.0V I_C=-16A	8			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	I_C=-8.0A I_B=-0.8A			-4	V
	$V_{CE(sat)(2)}$	I_C=-16A I_B=-3.2A			-6	V
Base to Emitter Voltage	V_{BE}	V_{CE}=-5.0V I_C=-8.0A			-2.2	V
Transition Frequency	f_T	V_{CE}=-10V I_C=-1A f=1.0MHz	4			MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V I_E=0 f=1.0MHz			500	pF


$I_C - V_{CE}$
30
25
20
15
I_C (A)
1.5 A
I_B = 2 A
1 A
0.5 A
$V_{BE} - I_C$
10
1.0
V_{BE} (V)
T_J = 25°C
V_{CE} = 20 V (SOLID)
V_{CE} = 5 V (DAS


TO-3P
单位：mm
A
R
C2
B1
B
A1
B2
b1
C
a1
C1
H

BR:

W21193

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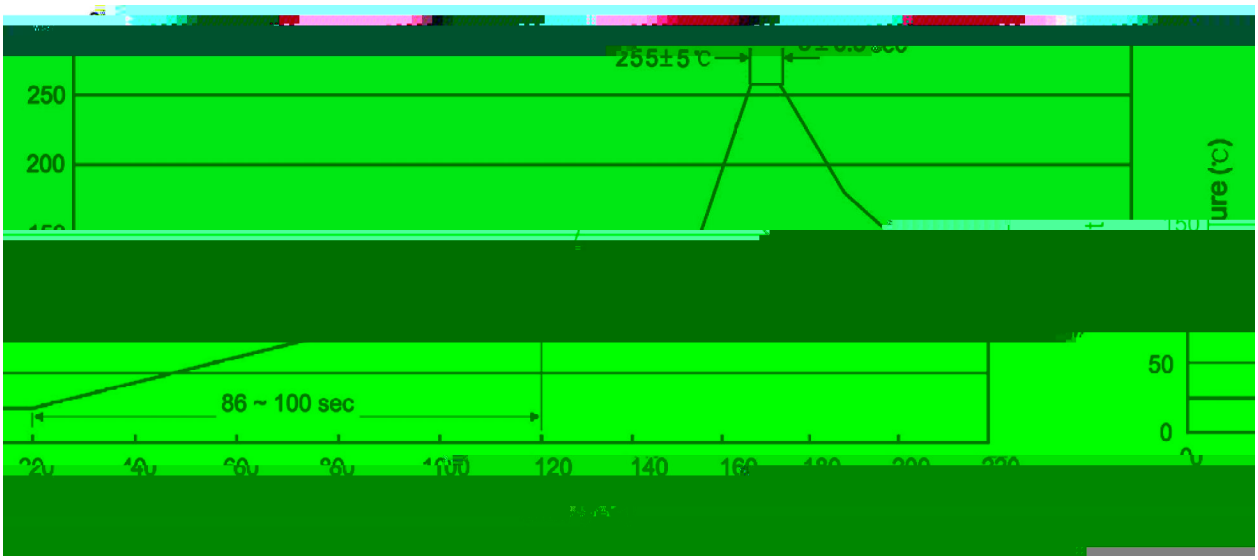
Note:

BR:	Company Code.
W21193:	Product Type.
****:	Lot No. Code, code change with Lot No.



				Note:	
1	25	150	60 90sec;	1.Preheating:25~150	, Time:60~90sec.
2	255±5		5±0.5sec;	2.Peak Temp.:255±5	, Duration:5±0.5sec.
3		2 10	/sec.	3. Cooling Speed: 2~10	/sec.

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ TUBE

Package Type	Units	Dimension	(unit mm^3)